

# Magnetic and electronic phases of $\text{U}_2\text{Rh}_3\text{Si}_5$

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## Motivation and scientific background

- Antiferromagnetic ground state (see Fig. 1) [1,2]
- Unique magnetic transition accompanied by a structural transition [1,2]
- Possible Explanation: Bootstrapping scenario [3]
- Here: Detailed study of the magnetic and electronic properties of  $\text{U}_2\text{Rh}_3\text{Si}_5$  [4]

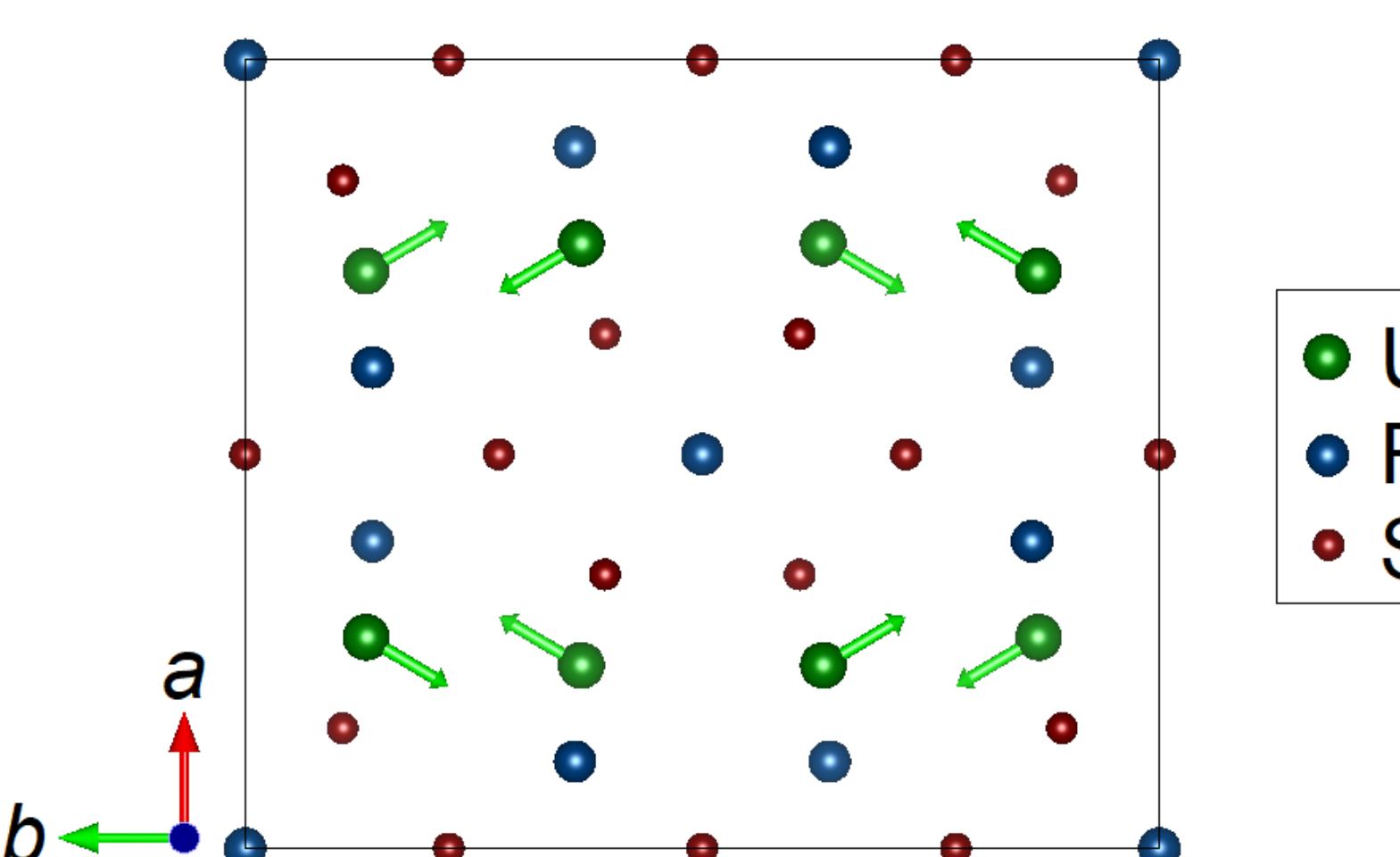


Fig. 1: Crystallographic and magnetic structure of  $\text{U}_2\text{Rh}_3\text{Si}_5$ .

## High-field measurements

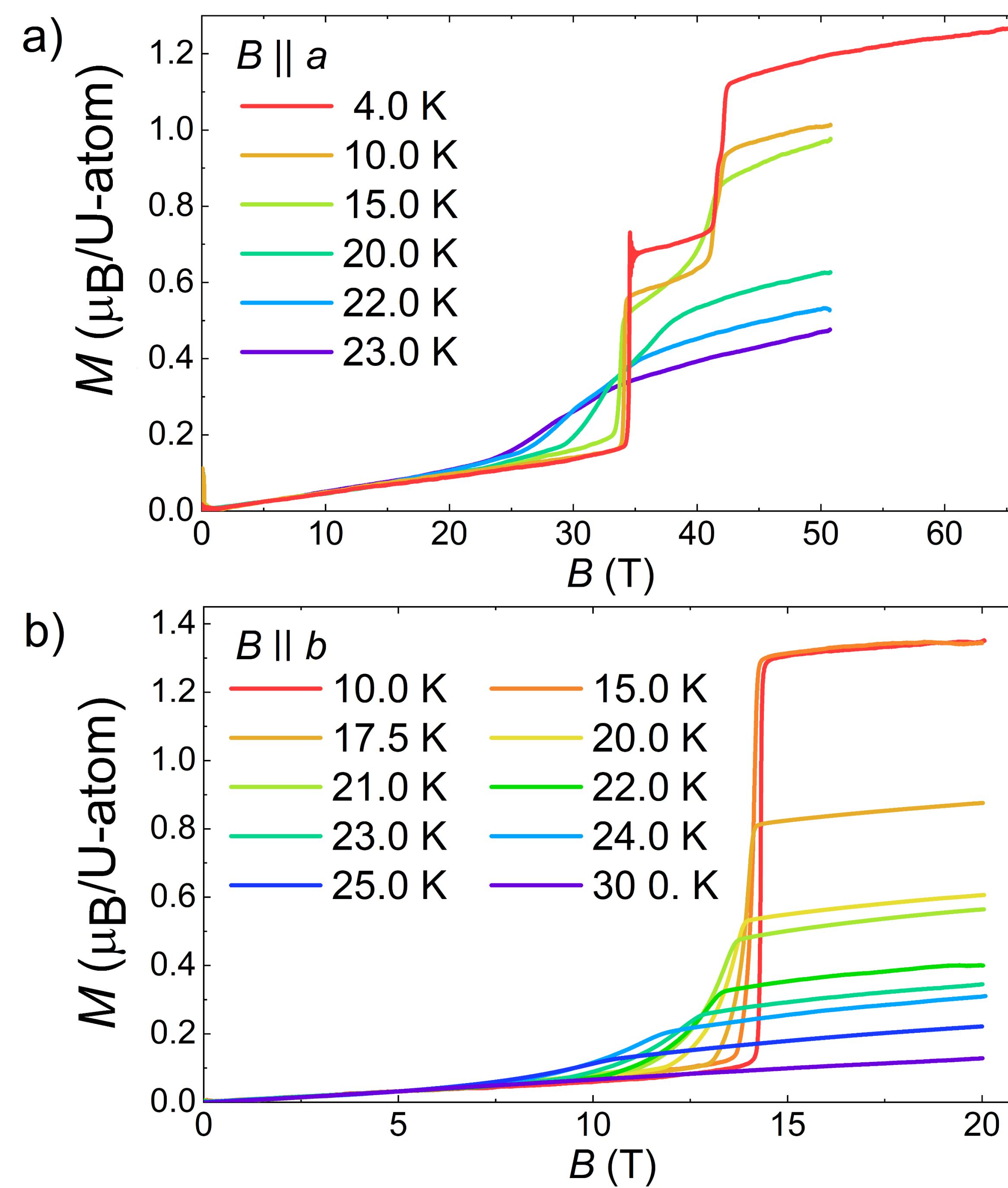


Fig. 2: Magnetization of  $\text{U}_2\text{Rh}_3\text{Si}_5$  in pulsed magnetic fields for (a)  $B \parallel a$  and (b)  $B \parallel b$ .

- Magnetization for  $B \parallel a$  and  $B \parallel b$  and magnetostriction of the  $b$  axis in pulsed magnetic fields (see Fig. 2, 3)
- Sharp jumps at transition fields
- First order transitions
- No phase transition measured for the  $c$  axis up to 65 T [4]
- Various steps in the magnetization of the  $a$  axis

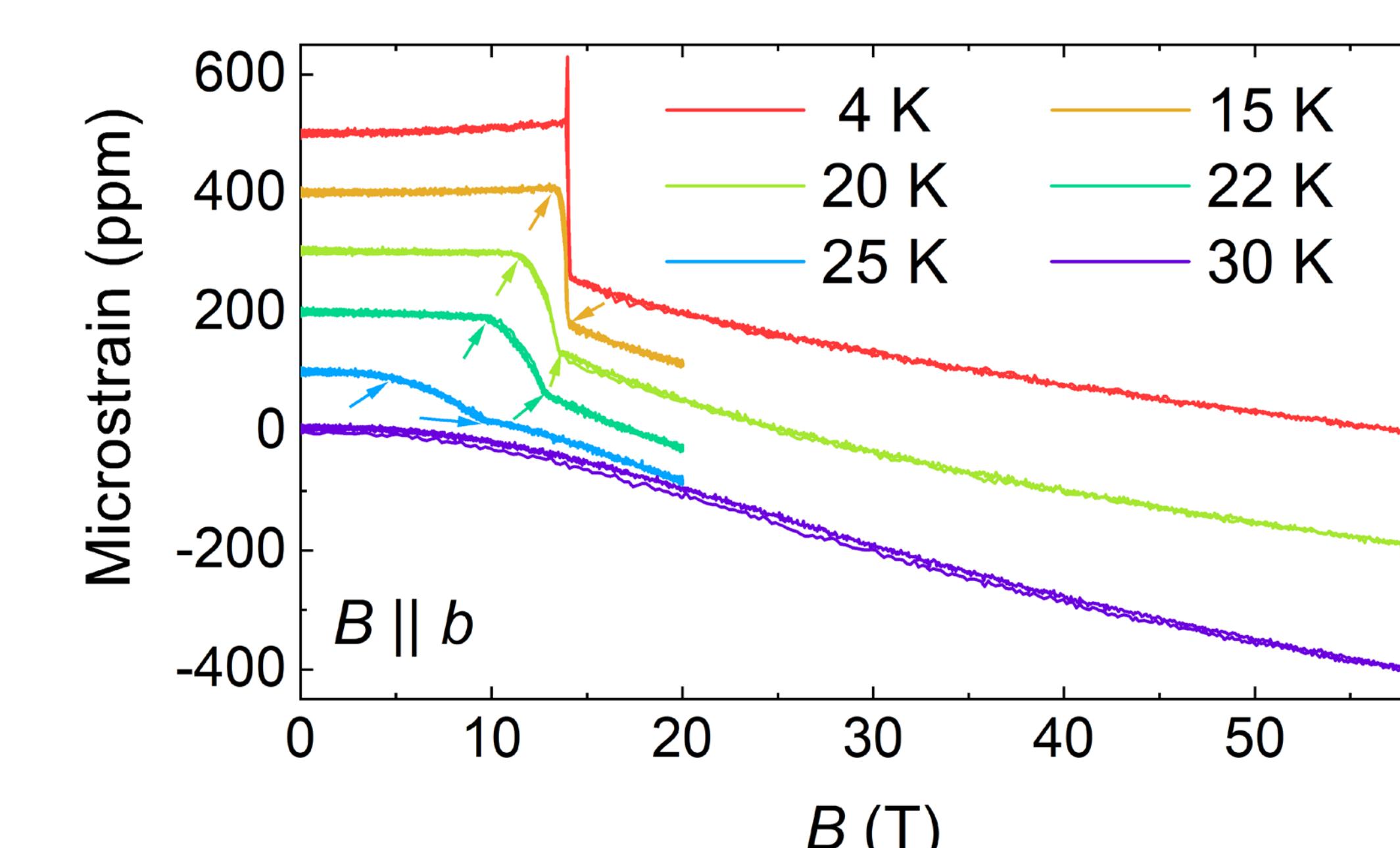


Fig. 3: Axial magnetostriction of  $\text{U}_2\text{Rh}_3\text{Si}_5$  for magnetic fields along the  $b$  axis.

## Literature:

- [1] B. Becker et al., Phys. Rev. Lett. **78**, 1347 (1997).
- [2] R. Feyerherm et al., Phys. Rev. B. **56**, 13693 (1997).
- [3] R. G. Leisure et al., Phys. Rev. Lett. **95**, 075506 (2005).
- [4] J. Willwater et al., Phys. Rev. B **103**, 054408 (2021).



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## Resistivity and susceptibility

- Two-step transition in the resistivity for all three axes ( $b$  axis shown in Fig. 4)
- Upturn at  $T^* = 26.5$  K and maximum at  $T_N = 26.0$  K

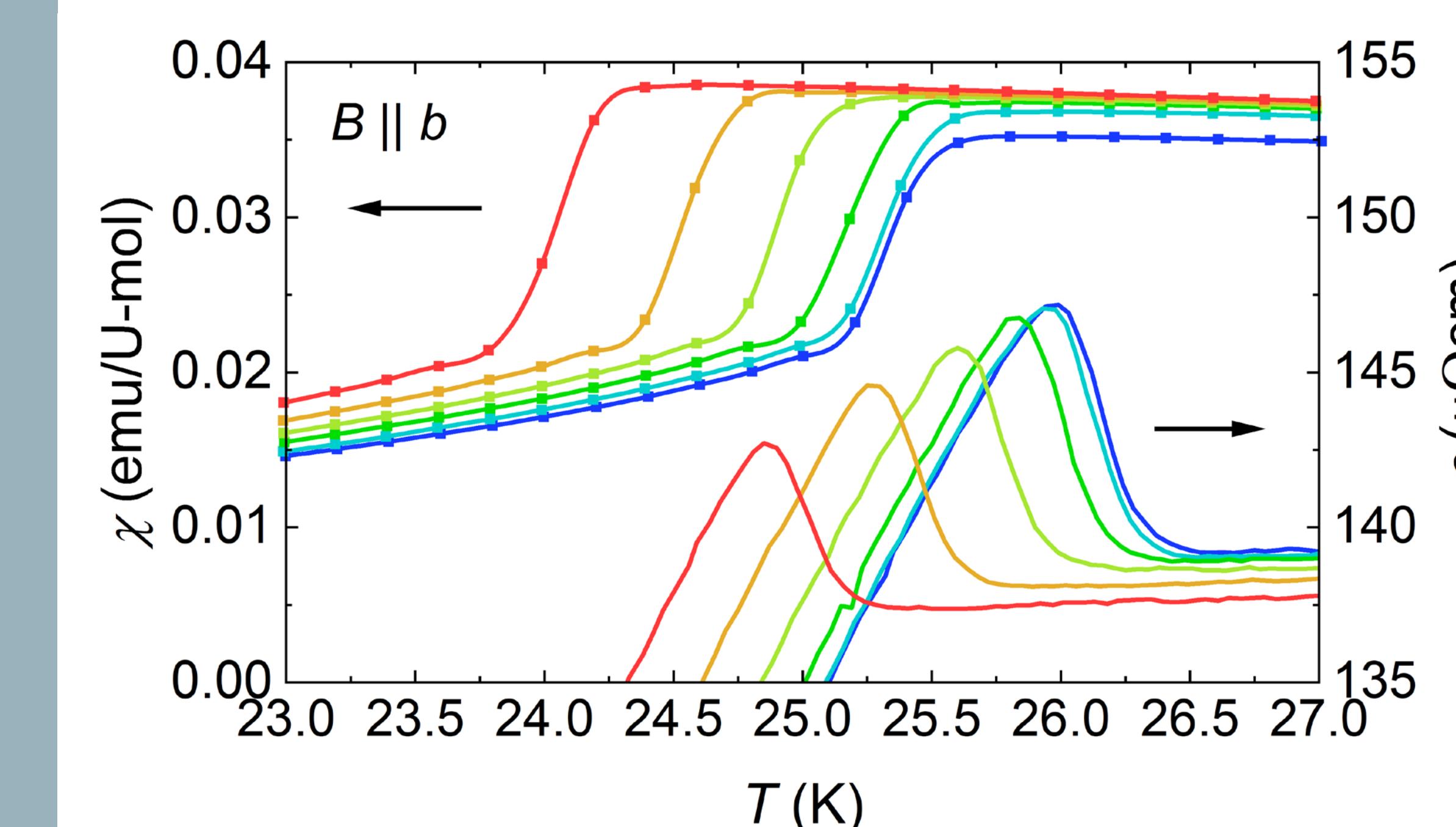


Fig. 4: Resistivity as a function of temperature for  $b$  axis.

- Comparison with the susceptibility (see Fig. 5):
  - No signature at  $T^*$  in the susceptibility or the structural parameters [4]
  - Drop of  $\chi$  at  $T_N \rightarrow$  magnetic transition

## Magnetic phase diagram

- Strongly anisotropic magnetic phase diagram (see Fig. 6)
- $a$  axis: Two additional high field phases  $\text{II}_{\text{a}}$  and  $\text{III}_{\text{a}}$  at low temperatures
  - Staircase scenario
- $b$  axis: Intermediate phase range  $\text{I}'_b$
- Additional feature in the resistivity at  $T^*$ 
  - Novel electronic phase  $\text{I}^{\text{EI}}$ ?
  - Interdependence of electronic, magnetic, and structural degrees of freedom in a bootstrapping scenario?
  - Further studies on electronic properties?
    - Hall effect, Seebeck effect, ...

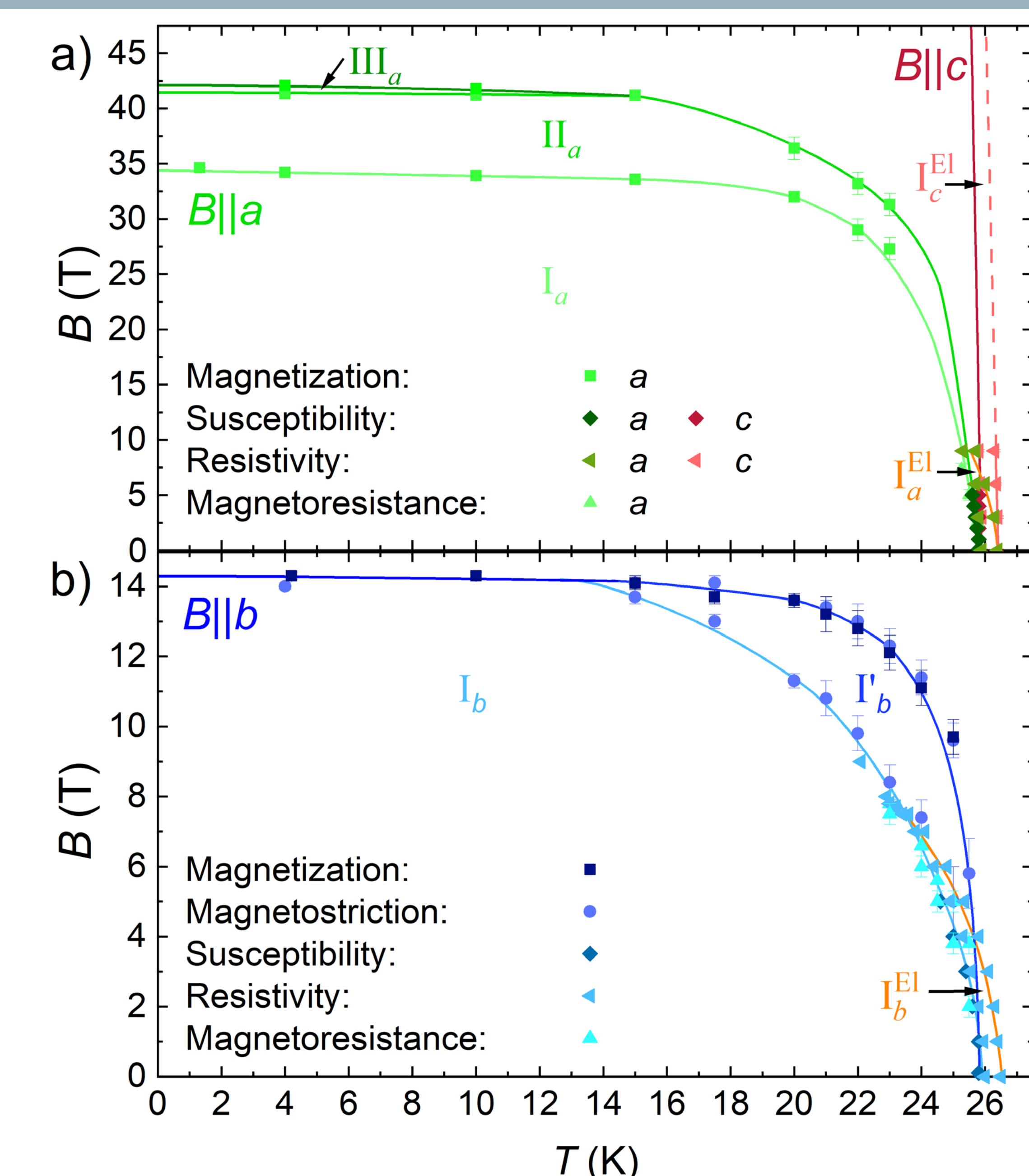


Fig. 6: Phase diagram of  $\text{U}_2\text{Rh}_3\text{Si}_5$  for (a) the  $a$  and  $c$  axes and (b) the  $b$  axis